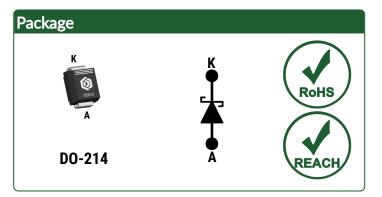
Silicon Carbide Schottky Diode

VRRM 1200 V **|**F (T_L ≤ 150°C) = 2 A **Q**c 11 nC

Features

- Low V_F for High Temperature Operation
- Enhanced Surge and Avalanche Robustness
- Superior Figure of Merit Q_C/I_F
- Low Thermal Resistance
- Low Reverse Leakage Current
- Temperature Independent Fast Switching
- Positive Temperature Coefficient of V_F
- High dV/dt Ruggedness



Advantages

- Improved System Efficiency
- High System Reliability
- Optimal Price Performance
- Reduced Cooling Requirements
- Increased System Power Density
- Zero Reverse Recovery Current
- Easy to Parallel without Thermal Runaway
- Enables Extremely Fast Switching

Applications

- High Voltage Sensing
- Solar Inverters
- Electric Vehicles
- High Frequency Converters
- Battery Chargers
- AC/DC Power Supplies
- Anti-Parallel / Free-Wheeling Diode
- LED and HID Lighting

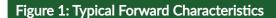
Absolute Maximum Ratings (At T _L = 25°C Unless Otherwise Stated)								
Parameter	Symbol	Conditions	Values	Unit	Note			
Repetitive Peak Reverse Voltage	V_{RRM}		1200	٧				
Continuous Forward Current	l _F	T _L ≤ 150°C	2	Α				
Non-Repetitive Peak Forward Surge Current, Half Sine Wave	I _{F,SM}	$T_L = 25^{\circ}C$, $t_P = 10 \text{ ms}$	20	٨				
		$T_L = 150$ °C, $t_P = 10$ ms	16	Α				
Repetitive Peak Forward Surge Current, Half Sine Wave	I _{F,RM}	$T_L = 25^{\circ}C$, $t_P = 10 \text{ ms}$	12	Α				
		$T_L = 150$ °C, $t_P = 10$ ms	9					
Non-Repetitive Peak Forward Surge Current	I _{F,MAX}	$T_L = 25^{\circ}C$, $t_P = 10 \mu s$	100	Α				
i ² t Value	∫i²dt	$T_L = 25^{\circ}C$, $t_P = 10 \text{ ms}$	2	A ² s				
Non-Repetitive Avalanche Energy	E _{AS}	L = 18.0 mH, I _{AS} = 2 A	36	mJ				
Diode Ruggedness	dV/dt	V _R = 0 ~ 960 V	200	V/ns				
Power Dissipation	P _{TOT}	T _L = 25°C	84	W	Fig. 3			
Operating and Storage Temperature	T _j , T _{stg}		-55 to 175	°C				



Electrical Characteristics								
Parameter	Symbol	Conditions -		Values			Unit	Note
	Syllibol			Min.	Тур.	Max.	Ullit	Note
Diode Forward Voltage	V_F	I _F = 2 A, T _j = 25°C			1.5	1.8	V	Fig. 1
	۷F	I _F = 2 A, T _j = 175°C			1.9			
Reverse Current	I-	V _R = 1200 V, T _j = 25°C			1	5	μΑ	Fig. 2
	I _R	$V_R = 1200 \text{ V, T}_j = 175^{\circ}\text{C}$			3			
Total Capacitive Charge	Qc		$V_{R} = 400 \text{ V}$		7		nC	Fig. 5
	Q C	$I_{F} \leq I_{F,MAX}$	$V_{R} = 800 V$		11		IIC	
Switching Time	+-	dI _F /dt = 200 A/μs	V _R = 400 V		< 10		no	
	ts		$V_{R} = 800 V$		< 10		ns	
Total Capacitance	C	V _R = 1 V, f = 1MHz			122		nE	Fig. 4
	C	V _R = 800 V, f = 1MHz			7		pF 	

Thermal/Package Characteristics								
Parameter	Symbol	Conditions	Values			Unia	Note	
			Min.	Тур.	Max.	- Unit	Note	
Thermal Resistance, Junction - Lead	R_{thJL}			5.17		°C/W		
Weight	W _T			0.3		g		





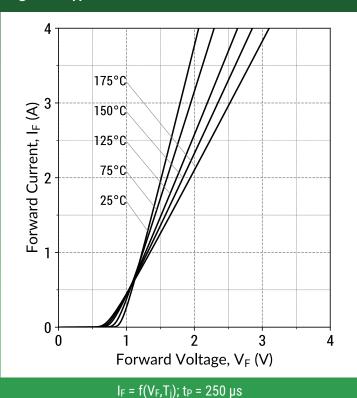
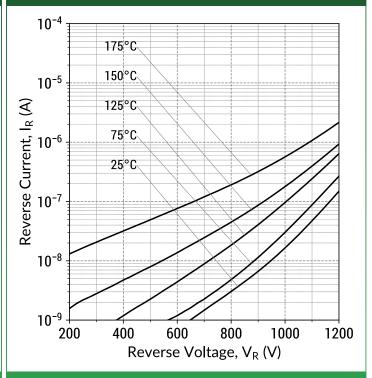


Figure 2: Typical Reverse Characteristics



 $I_R = f(V_R, T_j)$

Figure 3: Power Derating Curves

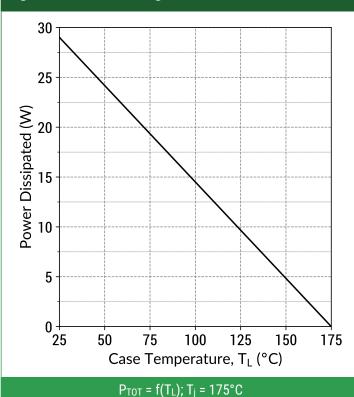
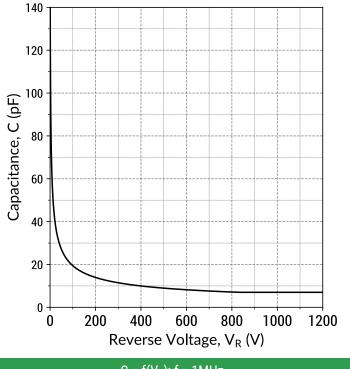


Figure 4: Typical Junction Capacitance vs Reverse Voltage Characteristics



 $C = f(V_R)$; f = 1MHz



Figure 5: Typical Capacitive Charge vs Reverse Voltage Characteristics

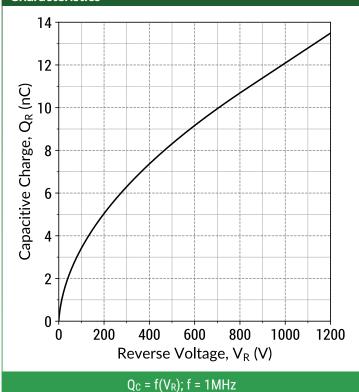
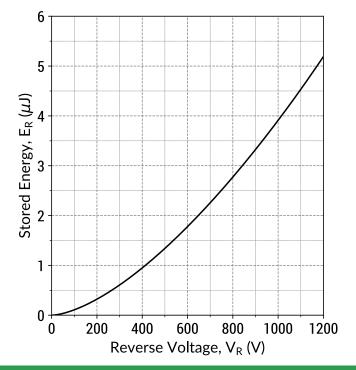
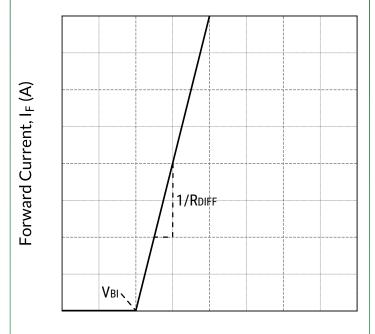


Figure 6: Typical Capacitive Energy vs Reverse Voltage Characteristics



 $E_C = f(V_R)$; f = 1MHz

Figure 7: Forward Curve Model



Forward Voltage, V_F (V)

 $I_F = f(V_F, T_j)$

Forward Curve Model Equation:

 $I_F = (V_F - V_{BI})/R_{DIFF}(A)$

Built-In Voltage (V_{BI}):

$$V_{BI}(T_j) = m \times T_j + n (V)$$

 $m = -0.00123 (V/^{\circ}C)$
 $n = 0.995 (V)$

Differential Resistance (RDIFF):

$$R_{DIFF}(T_j) = a \times T_j^2 + b \times T_j + c (\Omega)$$

 $a = 5.96e-06 (\Omega/^{\circ}C^2)$
 $b = 8.46e-04 (\Omega/^{\circ}C)$
 $c = 0.251 (\Omega)$

Forward Power Loss Equation:

 $P_{LOSS} = V_{BI}(T_j) \times I_{AVG} + R_{DIFF}(T_j) \times I_{RMS}^2$



Package Dimensions DO-214 Package Outline 0.155(3.940) 0.086(2.200) 0.130(3.300) 0.077(1.950) 0.180(4.570) 0.160(4.060) 0.096(2.440) 0.084(2.130)0.060(1.520) 0.008(0.203) 0.030(0.760) max 0.220(5.590) 0.205(5.210) Package View Recommended Solder Pad Layout 0.085(2.160) 0.085(2.160) min 0.107(2.740) max 0.089(2.260) max

NOTE

- 1. CONTROLLED DEIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
- 2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.





RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

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REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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